# **NPN Silicon Phototransistors**

## OP515A, OP515B, OP515C, OP515D, OP516A, OP516B, OP516C, OP516D

### Features:

- Variety of sensitivity ranges
- Coaxial leaded package style
- Small package size for space limited applications

#### **Description:**

Each device in the OP515 and OP516 series consists of NPN silicon phototransistors in a small hermetic package with an extended Collector lead. The narrow receiving angle provides excellent on-axis coupling. This device is 100% production tested using infrared light for close correlation with Optek's GaAs and GaAIAs emitters.

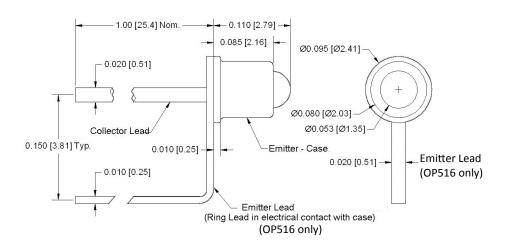
OP515

### Absolute Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise noted)

Continuous Collector Current	50 mA
Collector-Emitter Voltage	30V
Emitter-Collector Voltage (OP505 and OP506 series only)	5.0 V
Storage & Operating Temperature Range	-55°C to +125°C
Lead Soldering Temperature (1/16 inch (1.6 mm) from case for 5 sec. with soldering iron)	260°C <sup>(1)</sup>
Power Dissipation	100 mW <sup>(2)</sup>

#### Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering. Maximum 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 0.71 mW/°C above 25°C.



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

TT Electronics | OPTEK Technology 1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200 www.ttelectronics.com | sensors@ttelectronics.com



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Symbol	Parameter		Min	Тур	Max	Units	Test Conditions
I <sub>C(ON)</sub>	On-State Collector Current	OP515D/OP516D OP515C/OP516C OP515B/OP516B OP515A/OP516A	0.40 1.00 3.00 6.00			mA	$V_{CE} = 5 V, E_e = 5.0 \text{ mW/cm}^{2(3)}$
I <sub>CEO</sub>	Collector-Dark Current				100	nA	$V_{CE} = 10 \text{ V}, \text{ E}_{e} = 0^{(4)}$
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage		30			V	I <sub>C</sub> = 100 μA
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage		5			V	I <sub>E</sub> = 100 μA
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	OP515/OP516			0.40	V	$I_{C}$ = 400 µA, $E_{e}$ = 5.0 mW/cm <sup>2(3)</sup>
$\Delta I_{c} / \Delta T$	Relative $I_c$ Changes with Temperature OP505A-D and OP506A-D series			1.00		%/°C	$V_{CE} = 5 V, E_e = 1.0 mW/cm^2$
I <sub>ECO</sub>	Emitter-Reverse Curre	nt			100	μΑ	V <sub>EC</sub> = 0.4V

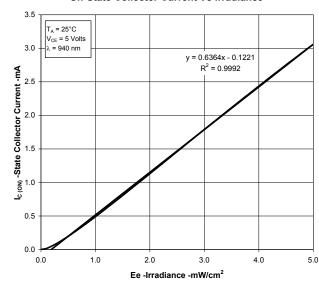
Notes:

E<sub>e(APT)</sub> is a measurement of the average apertured radiant energy incident upon a sensing area 0.250" (6.35mm) in diameter and (1) perpendicular to and centered to the mechanical axis of the emitting surface at a distance of 0.466" (11.84mm). E<sub>e(APT)</sub> is not necessarily uniform within the measured area.

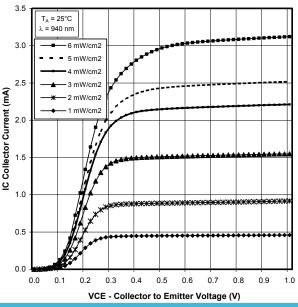
(2) Derating linearly 0.71 mW/°C above 25°C

(3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested. To calculate typical collector dark current in nA, use the formula  $I_{CED} = 10^{(0.040T} A^{-3.4)}$  where  $T_A$  is ambient temperature in °C.

(4)



**On-State Collector Current Vs Irradiance** 



Collector Current Vs Collector to Emitter Voltage vs Irradiance

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